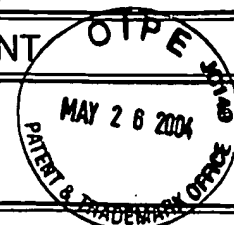


## ELECTRONIC INFORMATION DISCLOSURE STATEMENT

Electronic Version v18

Stylesheet Version v18.0



Title of Invention

TWIN EEPROM MEMORY TRANSISTORS WITH SUBSURFACE  
STEPPED FLOATING GATES

Application Number: 10/785160

Confirmation Number: 8504

First Named Applicant: Bohumil Lojek

Attorney Docket Number: ATM-303

Art Unit: 2811

Search string: ( 5424233 or 5917215 or 6043530 or 6323088 or 20020074583 ).pn.



## US Patent Documents

Note: Applicant is not required to submit a paper copy of cited US Patent Documents

init	Cite.No.	Patent No.	Date	Patentee	Kind	Class	Subclass
TDN	1	5424233	1995-06-13	Yang et al.	A1	437	43
TDN	2	5917215	1999-06-29	Chuang et al.	A1	257	321
TDN	3	6043530	2000-03-28	Chang	A1	257	320
TDN	4	6323088	2001-11-27	Gonzalez et al.	A1	438	257

## US Published Applications

Note: Applicant is not required to submit a paper copy of cited US Published Applications

init	Cite.No.	Pub. No.	Date	Applicant	Kind	Class	Subclass
TDN	1	20020074583	2002-06-20	Sugiyama et al.	A1	257	298

Signature

THANH T. NGUYEN

Examiner Name

Date

8/12/2005